74AXP1T57

Dual supply configurable multiple function gate

Rev. 2 — 22 December 2015 Product data sheet

1. General description

The 74AXP1T57 is a dual supply configurable multiple function gate with Schmitt-trigger inputs. It features three inputs (A, B and C), an output (Y) and dual supply pins (V_{CCI} and V_{CCO}). The inputs are referenced to V_{CCI} and the output is referenced to V_{CCO}. All inputs can be connected directly to V_{CCI} or GND. V_{CCI} can be supplied at any voltage between 0.7 V and 2.75 V and V_{CCO} can be supplied at any voltage between 1.2 V and 5.5 V. This feature allows voltage level translation. The 74AXP1T57 can be configured as any of the following logic functions AND, OR, NAND, NOR, XNOR, inverter and buffer.

This device ensures very low static and dynamic power consumption across the entire supply range and is fully specified for partial power down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the potentially damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range:
  - V_{CCI}: 0.7 V to 2.75 V
  - V_{CCO}: 1.2 V to 5.5 V
- Low input capacitance; C_I = 0.6 pF (typical)
- Low output capacitance; C_O = 1.8 pF (typical)
- Low dynamic power consumption; C_{PD} = 0.6 pF at V_{CCI} = 1.2 V (typical)
- Low dynamic power consumption; C_{PD} = 7.1 pF at V_{CCO} = 3.3 V (typical)
- Low static power consumption; I_{CCI} = 0.5 μA (85 °C maximum)
- Low static power consumption; I_{CCO} = 1.8 μA (85 °C maximum)
- High noise immunity
- Complies with JEDEC standard:
  - JESD8-12A.01 (1.1 V to 1.3 V; A, B, C inputs)
  - JESD8-11A.01 (1.4 V to 1.6 V)
  - JESD8-7A (1.65 V to 1.95 V)
  - JESD8-5A.01 (2.3 V to 2.7 V)
  - JESD8-C (2.7 V to 3.6 V; Y output)
  - JESD12-6 (4.5 V to 5.5 V; Y output)
- ESD protection:
  - HBM ANSI/ESDA/JEDEC JS-001 Class 2 exceeds 2 kV
  - CDM JESD22-C101E exceeds 1000 V
- Latch-up performance exceeds 100 mA per JESD78D Class II
- Inputs accept voltages up to 2.75 V
- Low noise overshoot and undershoot < 10 % of V_{CCO}

- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from −40 °C to +85 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AXP1T57DP	−40 °C to +85 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AXP1T57DC	−40 °C to +85 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AXP1T57GT	−40 °C to +85 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74AXP1T57GD	−40 °C to +85 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm	SOT996-2
74AXP1T57GN	−40 °C to +85 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116
74AXP1T57GS	−40 °C to +85 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203

4. Marking

Table 2. Marking

Type number	Marking code[1]
74AXP1T57DP	rD
74AXP1T57DC	rD
74AXP1T57GT	rD
74AXP1T57GD	rD
74AXP1T57GN	rD
74AXP1T57GS	rD

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

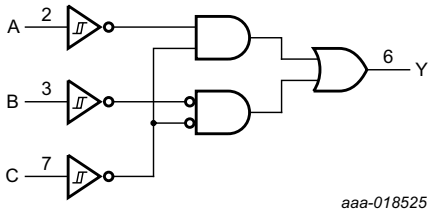


Fig 1. Logic symbol

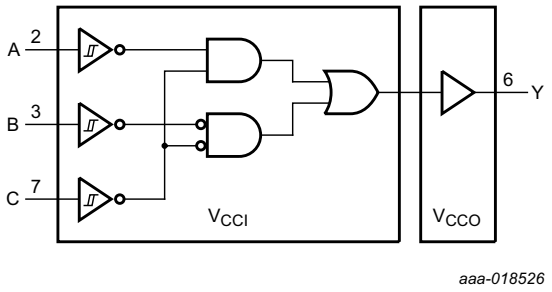


Fig 2. Logic diagram

6. Pinning information

6.1 Pinning

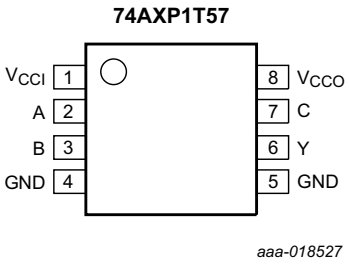


Fig 3. Pin configuration SOT505-2 and SOT765-1

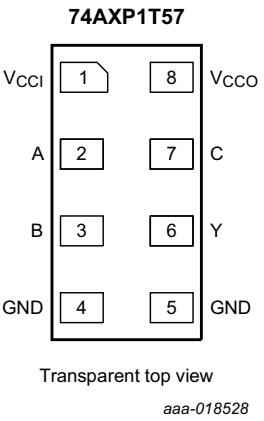


Fig 4. Pin configuration SOT833-1, SOT1116 and SOT1203

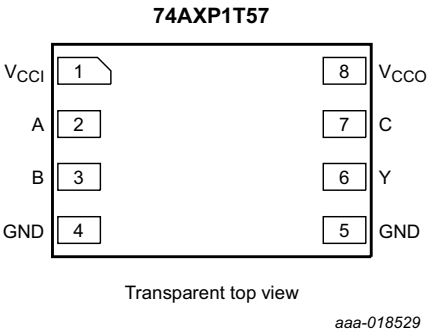


Fig 5. Pin configuration SOT996-2

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
V_{CCI}	1	input supply voltage
A, B, C	2, 3, 7	data input
GND[1]	4, 5	ground (0 V)
Y	6	data output
V_{CCO}	8	output supply voltage

[1] All GND pins must be connected to ground (0 V).

7. Functional description

Table 4. Function table[1]

Supply voltage		Input			Output
V_{CCI}	V_{CCO}	C	B	A	Y
0.7 V to 2.75 V	1.2 V to 5.5 V	L	L	L	H
0.7 V to 2.75 V	1.2 V to 5.5 V	L	L	H	L
0.7 V to 2.75 V	1.2 V to 5.5 V	L	H	L	H
0.7 V to 2.75 V	1.2 V to 5.5 V	L	H	H	L
0.7 V to 2.75 V	1.2 V to 5.5 V	H	L	L	L
0.7 V to 2.75 V	1.2 V to 5.5 V	H	L	H	L
0.7 V to 2.75 V	1.2 V to 5.5 V	H	H	L	H
0.7 V to 2.75 V	1.2 V to 5.5 V	H	H	H	H
GND	1.2 V to 5.5 V	X	X	X	Z
0.7 V to 2.75 V	GND	X	X	X	Z
GND	GND	X	X	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input AND	see Figure 6
2-input AND with both inputs inverted	see Figure 9
2-input NAND with inverted input	see Figure 7 and Figure 8
2-input OR with inverted input	see Figure 7 and Figure 8
2-input NOR	see Figure 9
2-input NOR with both inputs inverted	see Figure 6
2-input XNOR	see Figure 10
Inverter	see Figure 11
Buffer	see Figure 12

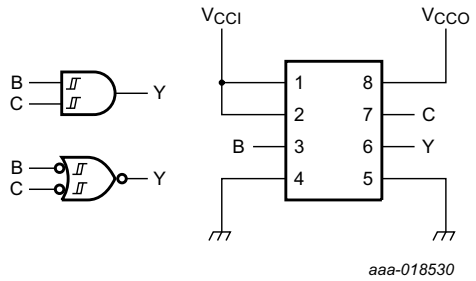


Fig 6. 2-input AND gate or 2-input NOR gate with both inputs inverted

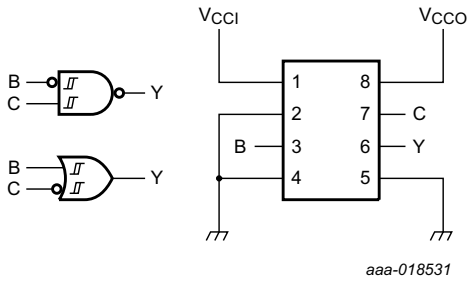


Fig 7. 2-input NAND gate with input B inverted or 2-input OR gate with inverted C input

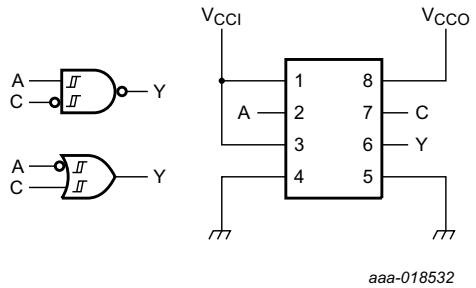


Fig 8. 2-input NAND gate with input C inverted or 2-input OR gate with inverted A input

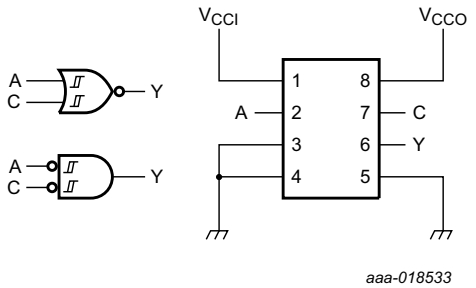


Fig 9. 2-input NOR gate or 2-input AND gate with both inputs inverted

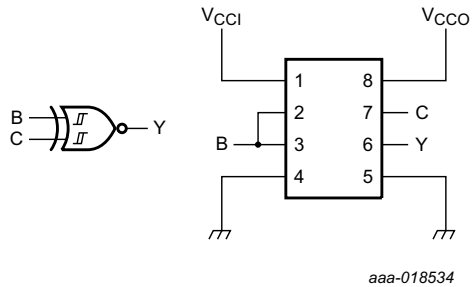


Fig 10. 2-input XNOR gate

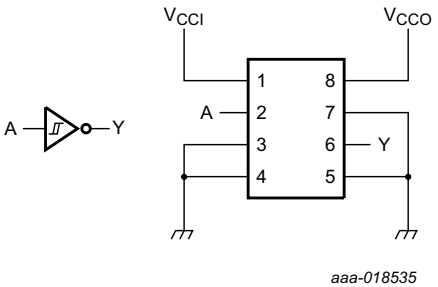


Fig 11. Inverter

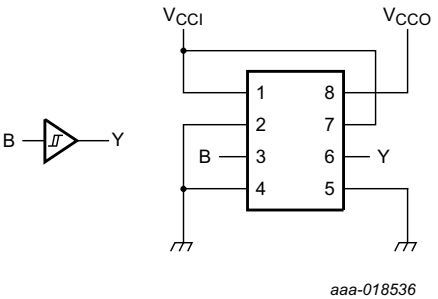


Fig 12. Buffer

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCI}	input supply voltage		–0.5	+3.3	V
V_{CCO}	output supply voltage		–0.5	+6.0	V
I_{IK}	input clamping current	$V_I < 0$ V	–50	-	mA
V_I	input voltage	[1]	–0.5	+3.3	V
I_{OK}	output clamping current	$V_O < 0$ V	–50	-	mA
V_O	output voltage	Active mode [1][2]	–0.5	V_{CCO} + 0.5	V
		Power-down or 3-state mode [1]	–0.5	+6.0	V
I_O	output current	V_O = 0 V to V_{CCO}	-	±25	mA
I_{CCI}	input supply current		-	50	mA
I_{CCO}	output supply current		-	50	mA
I_{GND}	ground current		–50	-	mA
T_{stg}	storage temperature		–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +85 °C	-	300	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} + 0.5 V should not exceed 6.0 V.

[3] For SOT505-2 package: above 100 °C the value of P_{tot} derates linearly with 4.7 mW/K.
For SOT833-1 package: above 70 °C the value of P_{tot} derates linearly with 3.2 mW/K.
For SOT1203 package: above 80 °C the value of P_{tot} derates linearly with 3.6 mW/K.

9. Recommended operating conditions

Table 7. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCI}	input supply voltage		0.7	2.75	V
V_{CCO}	output supply voltage		1.2	5.5	V
V_I	input voltage		0	2.75	V
V_O	output voltage	Active mode	0	V_{CCO}	V
		Power-down or 3-state mode	0	5.5	V
T_{amb}	ambient temperature		–40	+85	°C

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions, unless otherwise specified; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T_{amb} = –40 °C to +85 °C				Unit
			Min	Typ 25 °C	Max 25 °C	Max 85 °C	
V_{T+}	positive-going threshold voltage	see Figure 13 and Figure 14					
		V_{CCI} = 0.75 V to 0.85 V	$0.3V_{CCI}$	-	$0.8V_{CCI}$	$0.8V_{CCI}$	V
		V_{CCI} = 1.1 V to 1.95 V	$0.4V_{CCI}$	-	$0.7V_{CCI}$	$0.7V_{CCI}$	V
		V_{CCI} = 2.3 V to 2.7 V	0.9	-	1.7	1.7	V
V_{T-}	negative-going threshold voltage	see Figure 13 and Figure 14					
		V_{CCI} = 0.75 V to 0.85 V	$0.2V_{CCI}$	-	$0.7V_{CCI}$	$0.7V_{CCI}$	V
		V_{CCI} = 1.1 V to 1.95 V	$0.3V_{CCI}$	-	$0.6V_{CCI}$	$0.6V_{CCI}$	V
		V_{CCI} = 2.3 V to 2.7 V	0.7	-	1.5	1.5	V
V_H	hysteresis voltage	see Figure 13 and Figure 14					
		V_{CCI} = 0.75 V to 0.85 V	$0.06V_{CCI}$	-	$0.5V_{CCI}$	$0.5V_{CCI}$	V
		V_{CCI} = 1.1 V to 1.95 V	$0.1V_{CCI}$	-	$0.4V_{CCI}$	$0.4V_{CCI}$	V
		V_{CCI} = 2.3 V to 2.7 V	0.2	-	1.0	1.0	V
V_{OH}	HIGH-level output voltage	I_O = –2 mA; V_{CCO} = 1.2 V [1]	-	1.05	-	-	V
		I_O = –3 mA; V_{CCO} = 1.4 V	1.05	-	-	-	V
		I_O = –4.5 mA; V_{CCO} = 1.65 V	1.2	-	-	-	V
		I_O = –8 mA; V_{CCO} = 2.3 V	1.7	-	-	-	V
		I_O = –10 mA; V_{CCO} = 3.0 V	2.2	-	-	-	V
		I_O = –12 mA; V_{CCO} = 4.5 V	3.7	-	-	-	V
V_{OL}	LOW-level output voltage	I_O = 2 mA; V_{CCO} = 1.2 V [1]	-	0.18	-	-	V
		I_O = 3 mA; V_{CCO} = 1.4 V	-	-	0.35	0.35	V
		I_O = 4.5 mA; V_{CCO} = 1.65 V	-	-	0.45	0.45	V
		I_O = 8 mA; V_{CCO} = 2.3 V	-	-	0.7	0.7	V
		I_O = 10 mA; V_{CCO} = 3.0 V	-	-	0.8	0.8	V
		I_O = 12 mA; V_{CCO} = 4.5 V	-	-	0.8	0.8	V
I_I	input leakage current	V_I = 0 V to 2.75 V; V_{CCI} = 0 V to 2.75 V [1]	-	±0.001	±0.1	±0.5	µA
I_{OZ}	OFF-state output current	V_O = 0 V to 5.5 V; V_{CCO} = 1.2 V to 5.5 V	-	±0.001	±0.1	±0.5	µA

Table 8. Static characteristics *…continued*

At recommended operating conditions, unless otherwise specified; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T_{amb} = –40 °C to +85 °C				Unit
			Min	Typ 25 °C	Max 25 °C	Max 85 °C	
I_{OFF}	power-off leakage current	inputs; V_I = 0 V to 2.75 V; V_{CCI} = 0 V; V_{CCO} = 0 V to 5.5 V [1]	-	±0.01	±0.1	±0.5	µA
		output; V_O = 0 V to 5.5 V; V_{CCO} = 0 V; V_{CCI} = 0 V to 2.75 V; V_I = 0 V to 2.75 V [1]	-	±0.01	±0.1	±0.5	µA
ΔI_{OFF}	additional power-off leakage current	inputs; V_I = 0 V or 2.75 V; V_{CCI} = 0 V to 0.1 V; V_{CCO} = 0 V to 5.5 V [1]	-	±0.02	±0.1	±0.5	µA
		output; V_O = 0 V or 5.5 V; V_{CCO} = 0 V to 0.1 V; V_{CCI} = 0 V to 2.75 V; V_I = 0 V or 2.75 V [1]	-	±0.02	±0.1	±0.5	µA

[1] Typical values are measured at V_{CCI} = V_{CCO} = 1.2 V unless otherwise specified.

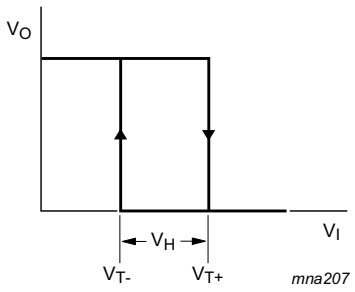


Fig 13. Transfer characteristic

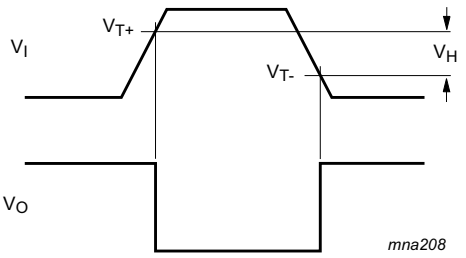


Fig 14. Definition of V_{T+}, V_{T-}, and V_H

Table 9. Static characteristics supply current

At recommended operating conditions, unless otherwise specified; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T_{amb} = –40 °C to +85 °C				Unit
			Typ 25 °C	Max 25 °C	Typ 85 °C	Max 85 °C	
I_{CCI}	input supply current	V_I = 0 V or V_{CCI};					
		V_{CCI} = 0.7 V to 1.3 V [1]	1	100	10	300	nA
		V_{CCI} = 1.3 V to 2.75 V [2]	1	100	20	500	nA
		V_{CCI} = 2.75 V; V_{CCO} = 0 V	1	100	20	500	nA
		V_{CCI} = 0 V; V_{CCO} = 5.5 V	1	100	1	100	nA
I_{CCO}	output supply current	V_I = 0 V or V_{CCI}; I_O = 0 A; see Table 10					
		V_{CCO} = 1.2 V to 3.6 V [1]	0.001	1.0	0.01	1.2	µA
		V_{CCO} = 3.6 V to 5.5 V [3]	0.8	1.5	1.0	1.8	µA
		V_{CCI} = 2.75 V; V_{CCO} = 0 V	0.001	0.1	0.003	0.2	µA
		V_{CCI} = 0 V; V_{CCO} = 3.6 V	0.2	0.6	0.3	0.8	µA
		V_{CCI} = 0 V; V_{CCO} = 5.5 V	0.4	0.8	0.5	1.0	µA
ΔI_{CCI}	additional input supply current	V_I = V_{CCI} – 0.5 V; V_{CCI} = 2.5 V	2	100	14	150	µA

[1] Typical values are measured at V_{CCI} = V_{CCO} = 1.2 V.

[2] Typical values are measured at V_{CCI} = V_{CCO} = 2.5 V.

[3] Typical values are measured at V_{CCI} = 1.2 V and V_{CCO} = 5.0 V.

Table 10. Typical output supply current (I_{CCO})

V_{CCI}	V_{CCO}							Unit
	0 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	
0 V	0	1	5	20	100	200	400	nA
0.8 V	1	10	150	200	300	500	800	nA
1.2 V	1	1	5	200	300	500	800	nA
1.5 V	1	1	5	100	300	500	800	nA
1.8 V	1	1	5	100	300	500	800	nA
2.5 V	1	1	5	100	100	500	800	nA

11. Dynamic characteristics

Table 11. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 22; for wave form, see Figure 15.

Symbol	Parameter	Conditions	V_{CCO}							Unit
			1.2 V	1.5 V ± 0.1 V			1.8 V ± 0.15 V			
			Typ[1]	Min	Typ[1]	Max	Min	Typ[1]	Max	
T_{amb} = 25 °C										
t_{pd}	propagation delay	A, B and C to Y [2]								
		V_{CCI} = 0.75 V to 0.85 V	25	4	20	76	4	18	72	ns
		V_{CCI} = 1.1 V to 1.3 V	16.5	3.4	10.9	21.0	3.0	8.9	17.0	ns
		V_{CCI} = 1.4 V to 1.6 V	15.5	3.1	9.9	19.0	2.6	7.9	14.0	ns
		V_{CCI} = 1.65 V to 1.95 V	15.0	2.6	9.4	18.0	2.1	7.4	12.5	ns
		V_{CCI} = 2.3 V to 2.7 V	14.5	2.7	8.9	17.5	2.2	6.9	11.7	ns
T_{amb} = –40 °C to +85 °C										
t_{pd}	propagation delay	A, B and C to Y [2]								
		V_{CCI} = 0.75 V to 0.85 V	25	3	20	151	3	18	148	ns
		V_{CCI} = 1.1 V to 1.3 V	16.5	3.4	10.9	21.0	3.0	8.9	17.0	ns
		V_{CCI} = 1.4 V to 1.6 V	15.5	3.1	9.9	19.0	2.6	7.9	14.0	ns
		V_{CCI} = 1.65 V to 1.95 V	15.0	2.6	9.4	18.0	2.1	7.4	12.5	ns
		V_{CCI} = 2.3 V to 2.7 V	14.5	2.7	8.9	17.5	2.2	6.9	11.7	ns
t_t	transition time	V_{CCI} = 0.75 V to 2.7 V [3]	-	1.0	-	-	1.0	-	-	ns

[1] Typical values are measured at nominal supply voltages and T_{amb} = +25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] t_t is the same as t_{THL} and t_{TLH}.

Table 12. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 22; for wave form, see Figure 15.

Symbol	Parameter	Conditions	V_{CCO}									Unit
			2.5 V ± 0.2 V			3.3 V ± 0.3 V			5.0 V ± 0.5 V			
			Min	Typ[1]	Max	Min	Typ[1]	Max	Min	Typ[1]	Max	
T_{amb} = 25 °C												
t_{pd}	propagation delay	A, B and C to Y [2]										
		V_{CCI} = 0.75 V to 0.85 V	3	16	72	3	16	80	3	17	92	ns
		V_{CCI} = 1.1 V to 1.3 V	2.6	7.3	12.0	2.5	6.7	10.7	2.4	6.4	10.2	ns
		V_{CCI} = 1.4 V to 1.6 V	2.3	6.2	9.9	2.1	5.6	9.0	2.1	5.3	8.5	ns
		V_{CCI} = 1.65 V to 1.95 V	1.7	5.7	9.3	1.6	5.1	8.3	1.5	4.8	7.9	ns
		V_{CCI} = 2.3 V to 2.7 V	1.9	5.2	8.7	1.8	4.6	7.7	1.7	4.3	7.2	ns
T_{amb} = –40 °C to +85 °C												
t_{pd}	propagation delay	A, B and C to Y [2]										
		V_{CCI} = 0.75 V to 0.85 V	2	16	167	2	16	194	2	17	225	ns
		V_{CCI} = 1.1 V to 1.3 V	2.6	7.3	12.0	2.5	6.7	10.7	2.4	6.4	10.2	ns
		V_{CCI} = 1.4 V to 1.6 V	2.3	6.2	9.9	2.1	5.6	9.0	2.1	5.3	8.5	ns
		V_{CCI} = 1.65 V to 1.95 V	1.7	5.7	9.3	1.6	5.1	8.3	1.5	4.8	7.9	ns
		V_{CCI} = 2.3 V to 2.7 V	1.9	5.2	8.7	1.8	4.6	7.7	1.7	4.3	7.2	ns
t_t	transition time	V_{CCI} = 0.75 V to 2.7 V [3]	1.0	-	-	1.0	-	-	1.0	-	-	ns

[1] Typical values are measured at nominal supply voltages and t_{amb} = +25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] t_t is the same as t_{THL} and t_{TLH}.

Table 13. Typical dynamic characteristics at T_{amb} = 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 22; for wave form, see Figure 15.

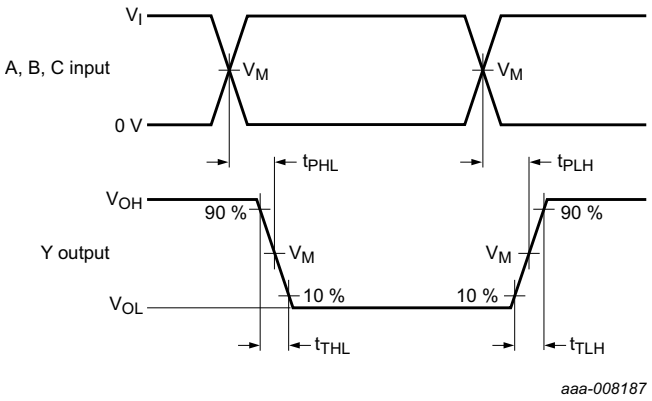
Symbol	Parameter	Conditions	V_{CCO}						Unit
			1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	
C_{PD}	power dissipation capacitance	f_i = 1 MHz; R_L = ∞ Ω; V_I = 0 V to V_{CCI} [1]							
		input supply [2]							
		V_{CCI} = 0.8 V	0.5	0.5	0.5	0.5	0.5	0.5	pF
		V_{CCI} = 1.2 V	0.6	0.6	0.6	0.6	0.6	0.6	pF
		V_{CCI} = 1.5 V	0.7	0.7	0.7	0.7	0.7	0.7	pF
		V_{CCI} = 1.8 V	0.8	0.8	0.8	0.8	0.8	0.8	pF
		V_{CCI} = 2.5 V	1.0	1.0	1.0	1.0	1.0	1.0	pF
		output supply [3]							
		V_{CCI} = 0.8 V	6.7	6.8	6.8	6.9	7.5	9.5	pF
		V_{CCI} = 1.2 V	6.8	6.9	7.0	7.0	7.1	7.6	pF
		V_{CCI} = 1.5 V	6.9	6.9	6.9	7.0	7.1	7.6	pF
		V_{CCI} = 1.8 V	6.9	6.9	6.9	7.0	7.2	7.6	pF
		V_{CCI} = 2.5 V	6.9	7.0	7.0	7.0	7.2	7.6	pF
C_I	input capacitance	V_I = 0 V or V_{CCI}; V_{CCI} = 0 V to 2.7 V	0.6	0.6	0.6	0.6	0.6	0.6	pF
C_O	output capacitance	V_O = 0 V; V_{CCO} = 0 V	1.8	1.8	1.8	1.8	1.8	1.8	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

[2] Power dissipated from input supply (V_{CCI})
$P_D = C_{PD} \times V_{CCI}^2 \times f_i \times N$ where:
C_{PD} = power dissipation capacitance of the input supply.
V_{CCI} = input supply voltage in V;
f_i = input frequency in MHz;
N = number of inputs switching;

[3] Power dissipated from output supply (V_{CCO})
$P_D = (C_L + C_{PD}) \times V_{CCO}^2 \times f_o$ where:
C_L = load capacitance in pF;
C_{PD} = power dissipation capacitance of the output supply.
V_{CCO} = output supply voltage in V;
f_o = output frequency in MHz;

11.1 Waveforms and graphs



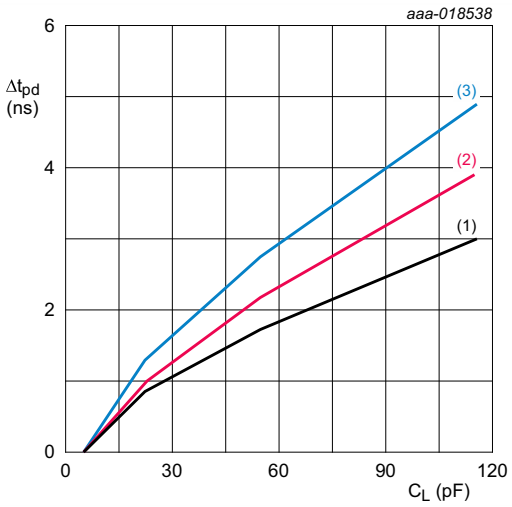
Measurement points are given in Table 14.

V_{OL} and V_{OH} are typical output voltage drops that occur with the output load.

Fig 15. Input A, B and C to output Y propagation delay times and output transition times

Table 14. Measurement points

Supply voltage		Output	Input	
V_{CCI}	V_{CCO}	V_M	V_M	V_I
0.75 V to 2.7 V	1.2 V to 5.5 V	$0.5V_{CCO}$	$0.5V_{CCI}$	V_{CCI}



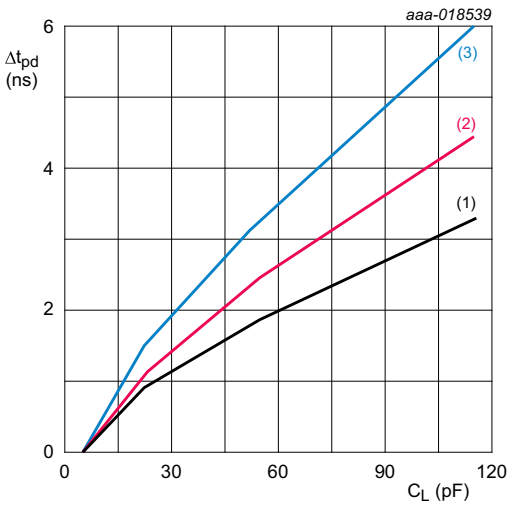
T_{amb} = −40 °C to +85 °C unless otherwise specified.

(1) Minimum: V_{CCO} = 5.5 V

(2) Typical: T_{amb} = 25 °C; V_{CCO} = 5 V

(3) Maximum: V_{CCO} = 4.5 V

Fig 16. Additional propagation delay versus load capacitance



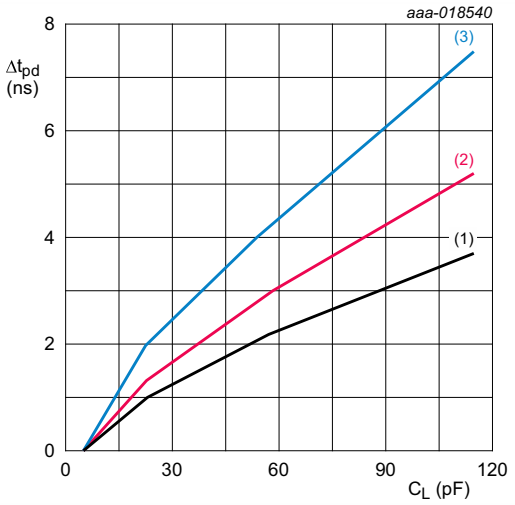
T_{amb} = −40 °C to +85 °C unless otherwise specified.

(1) Minimum: V_{CCO} = 3.6 V

(2) Typical: T_{amb} = 25 °C; V_{CCO} = 3.3 V

(3) Maximum: V_{CCO} = 3 V

Fig 17. Additional propagation delay versus load capacitance



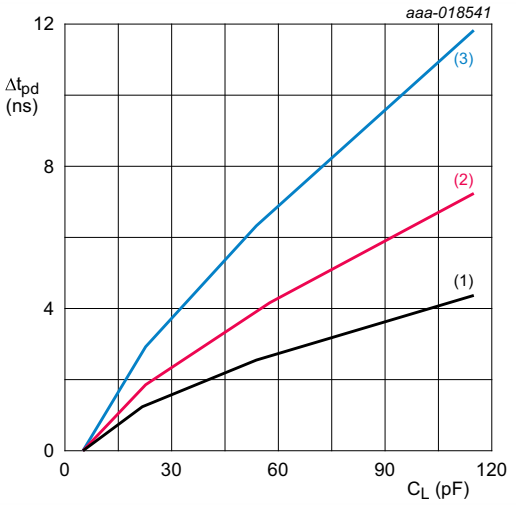
T_{amb} = –40 °C to +85 °C unless otherwise specified.

(1) Minimum: V_{CCO} = 2.7 V

(2) Typical: T_{amb} = 25 °C; V_{CCO} = 2.5 V

(3) Maximum: V_{CCO} = 2.3 V

Fig 18. Additional propagation delay versus load capacitance



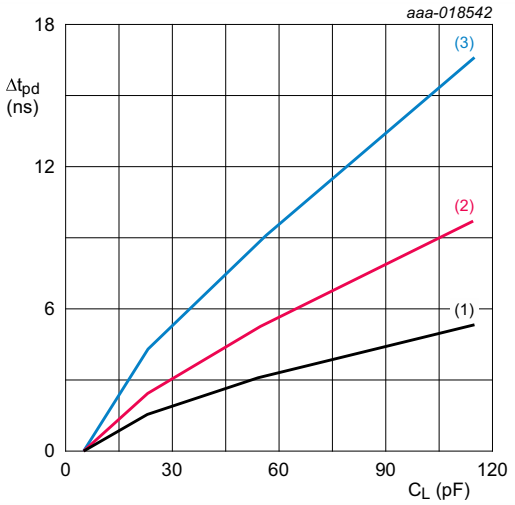
T_{amb} = –40 °C to +85 °C unless otherwise specified.

(1) Minimum: V_{CCO} = 1.95 V

(2) Typical: T_{amb} = 25 °C; V_{CCO} = 1.8 V

(3) Maximum: V_{CCO} = 1.65 V

Fig 19. Additional propagation delay versus load capacitance



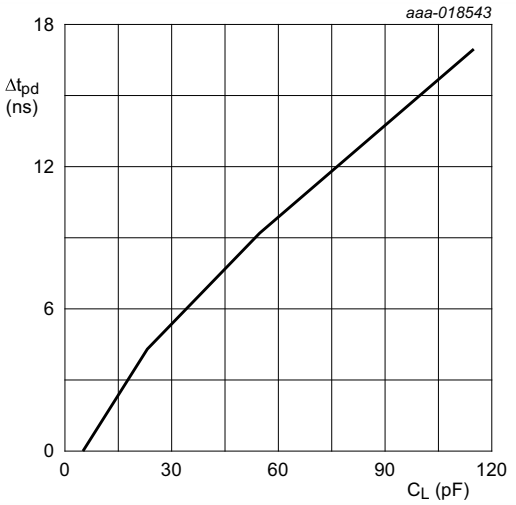
T_{amb} = –40 °C to +85 °C unless otherwise specified.

(1) Minimum: V_{CCO} = 1.6 V

(2) Typical: T_{amb} = 25 °C; V_{CCO} = 1.5 V

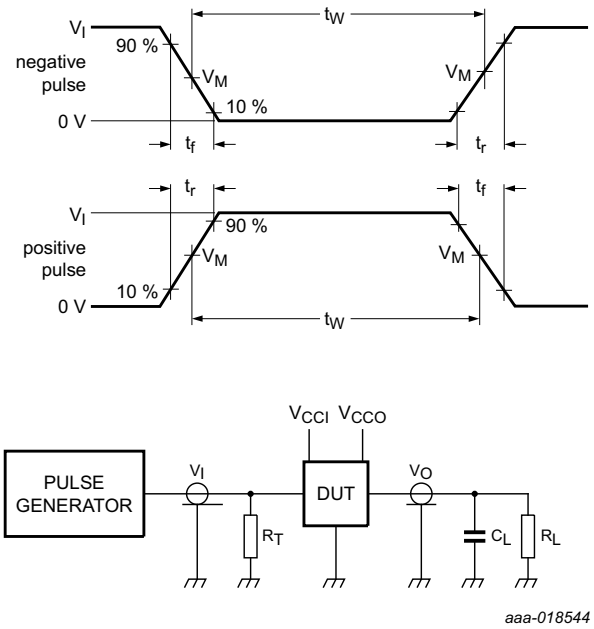
(3) Maximum: V_{CCO} = 1.4 V

Fig 20. Additional propagation delay versus load capacitance



T_{amb} = 25 °C; V_{CCO} = 1.2 V.

Fig 21. Additional propagation delay versus load capacitance



Test data is given in Table 15.

Definitions test circuit:

R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

R_L = Load resistance.

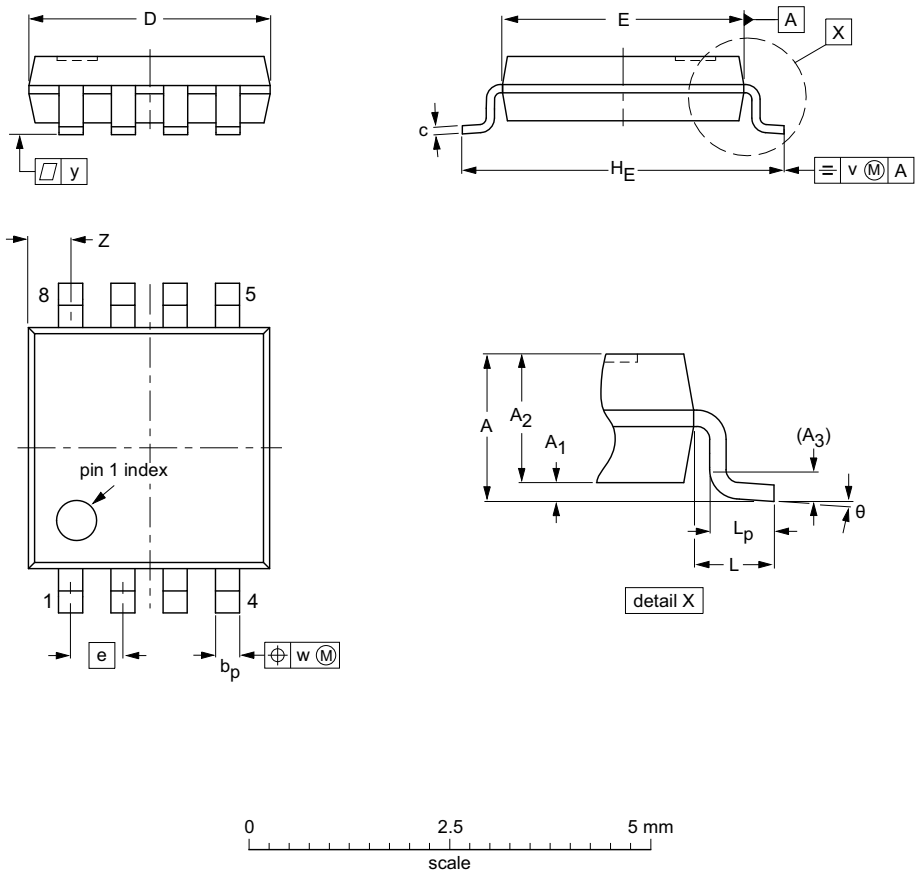
Fig 22. Test circuit for measuring switching times

Table 15. Test data

Supply voltage		Load		Input	
V_{CCI}	V_{CCO}	C_L	R_L	t_r, t_f	V_I
0.75 V to 2.7 V	1.2 V to 5.5 V	5 pF	5 kΩ	≤3.0 ns	V_{CCI}

12. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

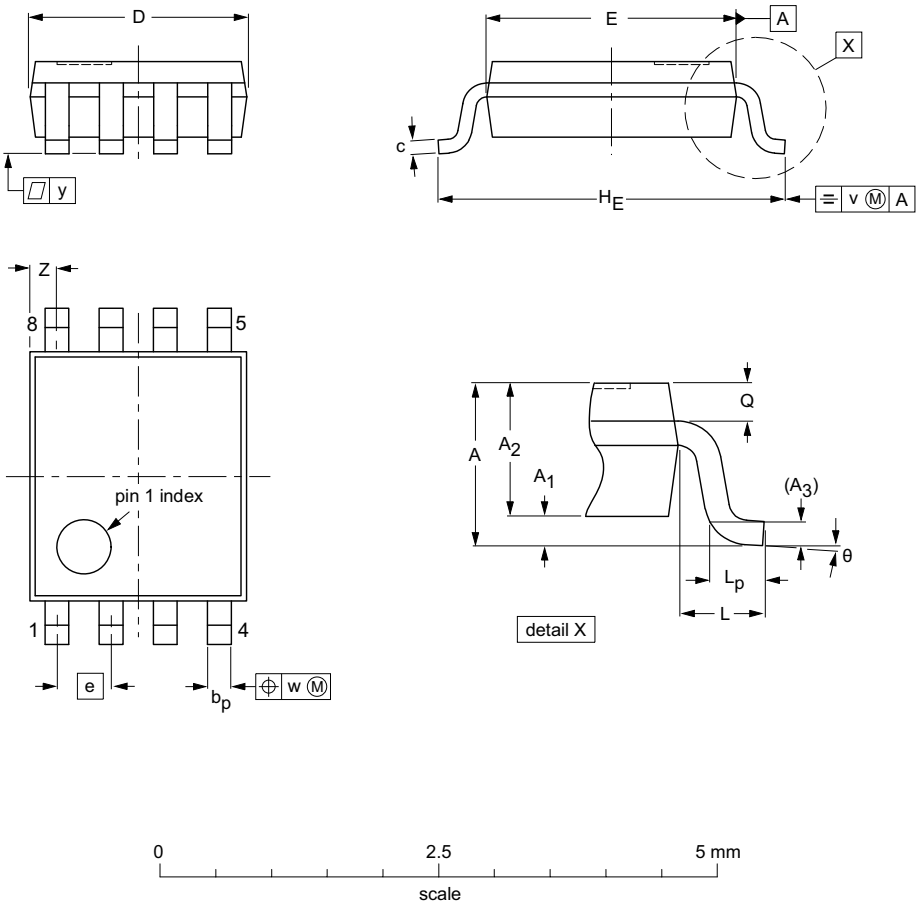
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 23. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

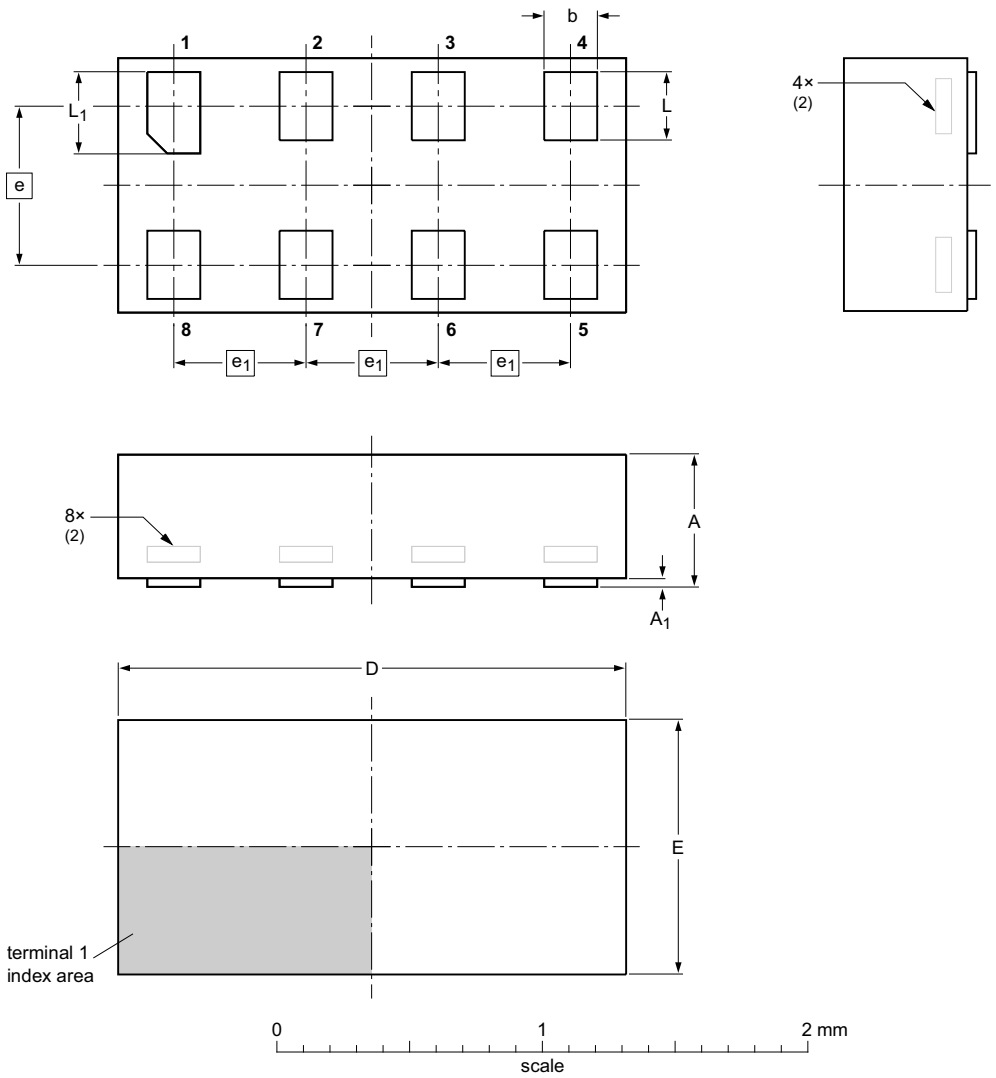
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 24. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm **SOT833-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.25 0.17	2.0 1.9	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

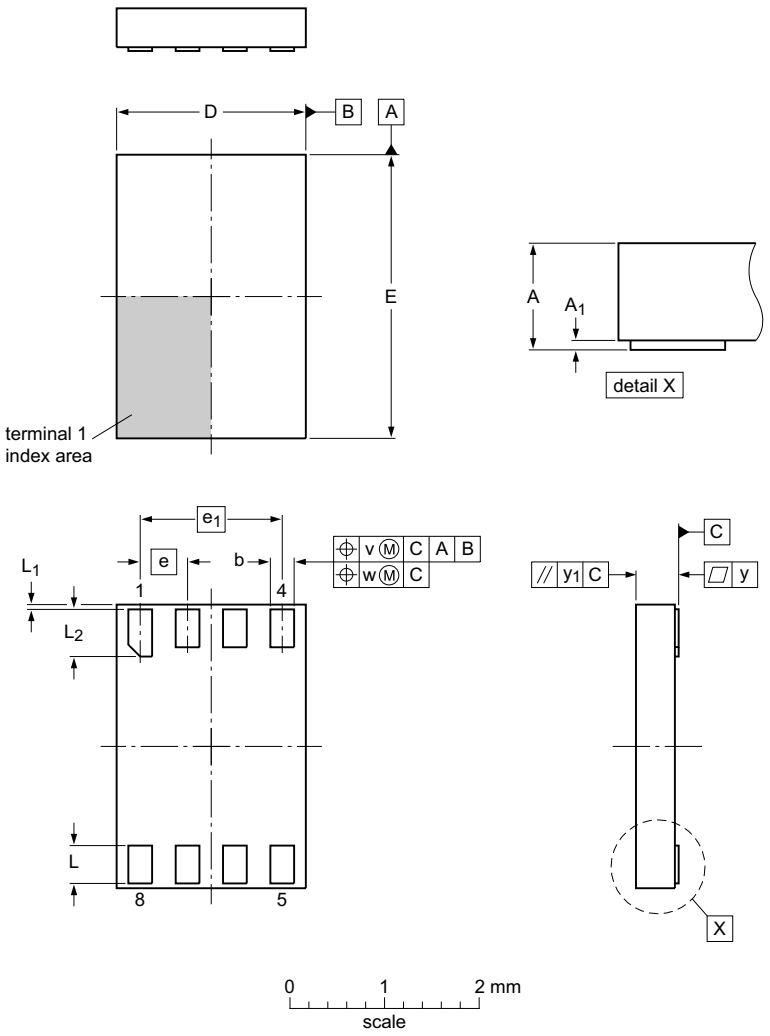
Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT833-1	- - -	MO-252	- - -			~~07-11-14~~ 07-12-07

Fig 25. Package outline SOT833-1 (XSON8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm **SOT996-2**



Dimensions (mm are the original dimensions)

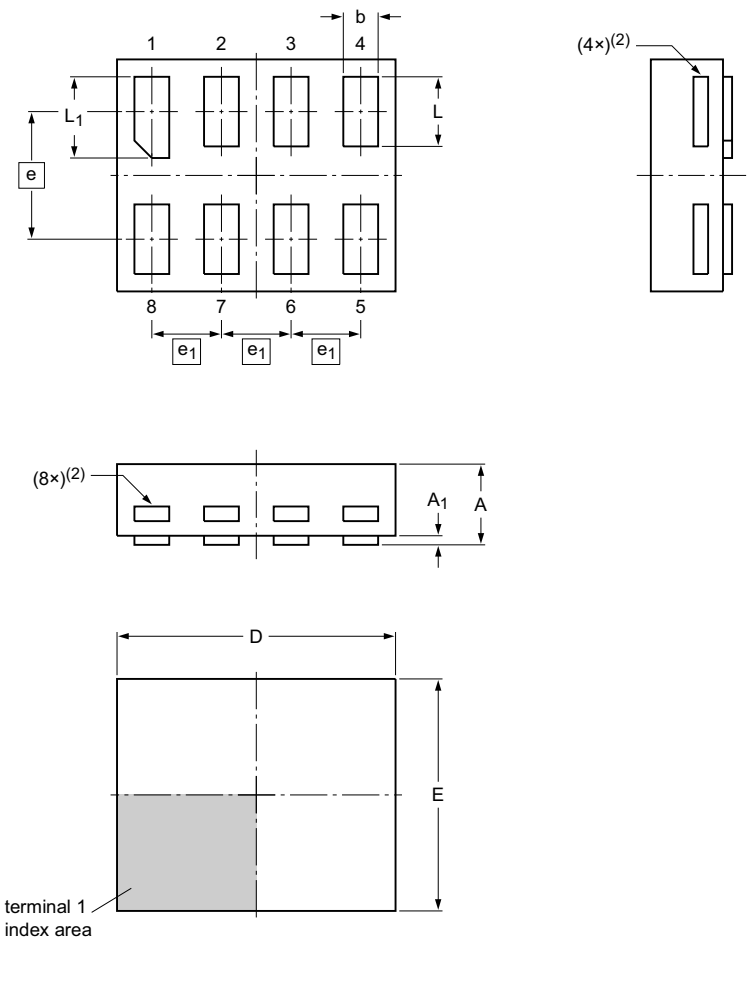
Unit[1]		A	A_1	b	D	E	e	e_1	L	L_1	L_2	v	w	y	y_1
mm	max		0.05	0.35	2.1	3.1			0.5	0.15	0.6				
	nom	0.5					0.5	1.5				0.1	0.05	0.05	0.1
	min		0.00	0.15	1.9	2.9			0.3	0.05	0.4				

sot996-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT996-2						~~07-12-21~~ 12-11-20

Fig 26. Package outline SOT996-2 (XSON8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.2 x 1.0 x 0.35 mm **SOT1116**



Dimensions

Unit		$A^{(1)}$	A_1	b	D	E	e	e_1	L	L_1
mm	max	0.35	0.04	0.20	1.25	1.05			0.35	0.40
	nom			0.15	1.20	1.00	0.55	0.3	0.30	0.35
	min			0.12	1.15	0.95			0.27	0.32

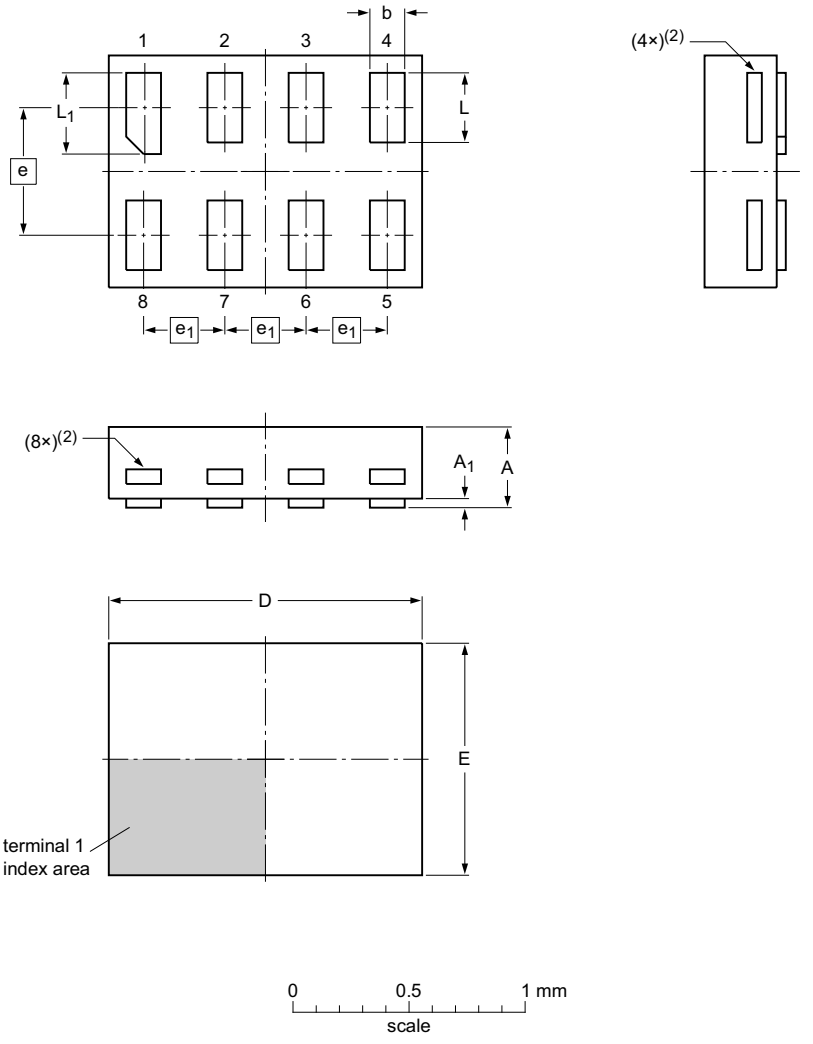
Note
1. Including plating thickness.
2. Visible depending upon used manufacturing technology.

sot1116_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1116						~~10-04-02~~ 10-04-07

Fig 27. Package outline SOT1116 (XSON8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1.0 x 0.35 mm **SOT1203**



Dimensions

Unit		$A^{(1)}$	A_1	b	D	E	e	e_1	L	L_1
mm	max	0.35	0.04	0.20	1.40	1.05			0.35	0.40
	nom			0.15	1.35	1.00	0.55	0.35	0.30	0.35
	min			0.12	1.30	0.95			0.27	0.32

Note
1. Including plating thickness.
2. Visible depending upon used manufacturing technology.

sot1203_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1203						~~10-04-02~~ 10-04-06

Fig 28. Package outline SOT1203 (XSON8)

13. Abbreviations

Table 16. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model

14. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AXP1T57 v.2	20151222	Product data sheet	-	74AXP1T57 v.1
Modifications:	• Table 6: Conditions V_O corrected (errata). • Table 6: Derating values for packages added (errata). • Table 7: Conditions V_O corrected (errata). • Table 8: Conditions I_{OZ} corrected (errata). • Table 9: Conditions ΔI_{CCI} corrected (errata). • Table 11 and Table 12: Conditions t_τ corrected (errata). • Table 11: Conditions t_τ corrected (errata). • Table 13: Removed “leadless packages” from conditions (errata).			
74AXP1T57 v.1	20150803	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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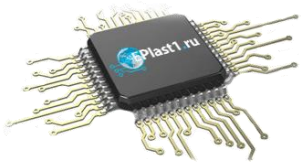
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.